

LIST OF PUBLICATIONS

- **Z. Y. Tung**, D. S. Ang, and Y. Gao, “On electron-trap transformation and its unexpected frequency dependence under dynamic positive-bias temperature stressing,” in Proceedings IEEE International Reliability Physics Symposium (IRPS), Jun. 2014, pp. XT.10.1–XT.10.6, doi: 10.1109/IRPS.2014.6861187.
- **Z. Y. Tung** and D. S. Ang, “Transient to temporarily permanent and permanent hole trapping transformation in the small area SiON P-MOSFET subjected to negative-bias temperature stress,” in Proceedings IEEE 21st International Symposium on the Physical and Failure Analysis of Integrated Circuits (IPFA), Jun./Jul. 2014, pp. 254–257, doi: 10.1109/IPFA.2014.6898197.
- **Z. Y. Tung**, and D. S. Ang, “Alteration of Oxide-Trap Switching Activity at Operating Condition by Voltage-Accelerated Stressing,” in Proceedings IEEE International Reliability Physics Symposium (IRPS), Apr. 2016, pp. XT.01.1–XT.01.3, doi: 10.1109/IRPS.2016.7574643.
- **Z. Y. Tung** and D. S. Ang, “Impact of Voltage-Accelerated Stress on Hole Trapping at Operating Condition,” IEEE Electron Device Letters, vol. 37, no. 5, pp. 644–647, May 2016, doi: 10.1109/LED.2016.2543239.
- A. A. Boo, **Z. Y. Tung**, and D. S. Ang, “New Observations on the Correlation Between Hole-Trapping Transformation and SILC Generation Under NBTI Stressing,” IEEE Electron Device Letters, vol. 37, no. 4, pp. 369–372, April 2016, doi: 10.1109/LED.2016.2531752.
- D. S. Ang, C. J. Gu, **Z. Y. Tung**, A. A. Boo, and Y. Gao, “Evolution of oxide charge trapping under bias temperature stressing,” Microelectronics Reliability, vol. 54, no. 4, pp. 663–681, Apr. 2014, doi: 10.1016/j.microrel.2014.01.025.